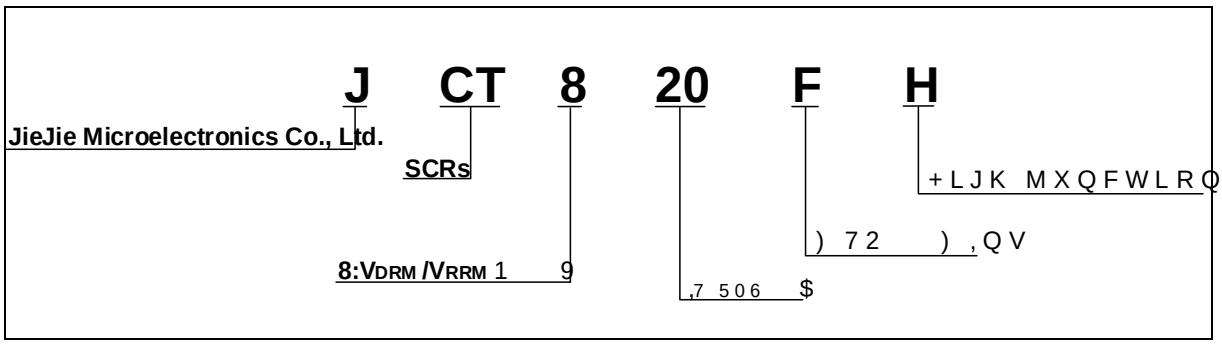
Average gate power dissipation (T$_j$=150		3* $9		
3HDN JDWH SRZHU		3*0		:
3HDN SXOVH YROWDJH QRQ UHSHWLWLYH RII VWDWH),*	7M	9SS		

> dZ/ > , Z d ZT/j=25 / X^QOHVV RWKHUZLVH VSHFLILHG

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D = 12V R_L = 33 Ω	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	V_D = V_{DRM} T_j = 150				

h w5 9 wLbD LbC h wa ! ¢ L h b



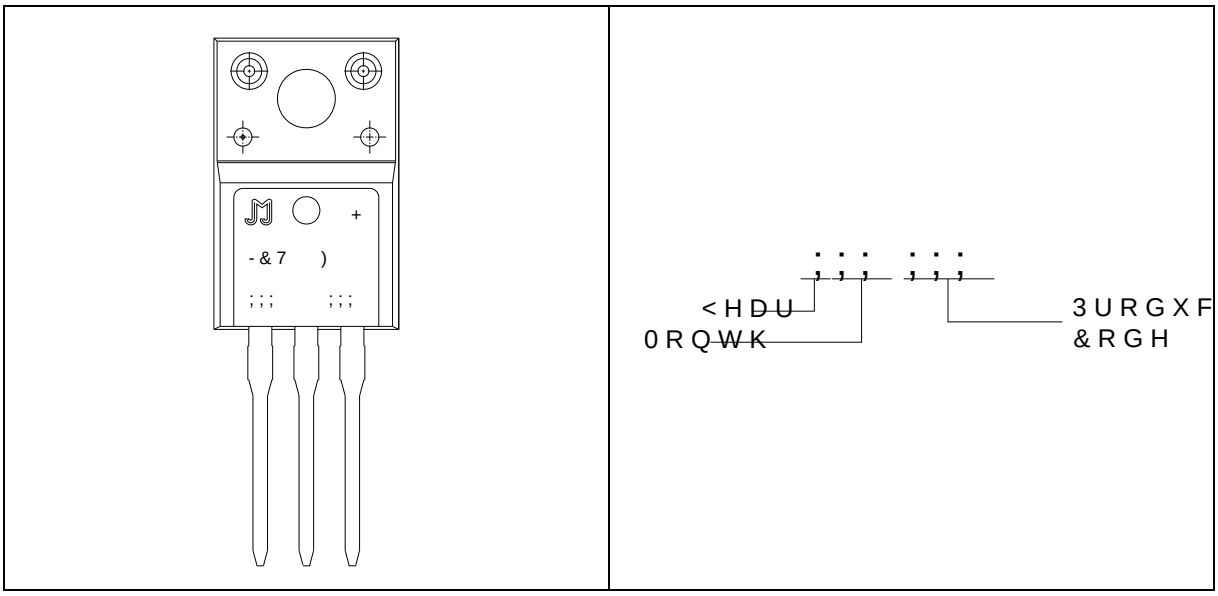


FIG.1: Maximum power dissipation versus RMS on-state current

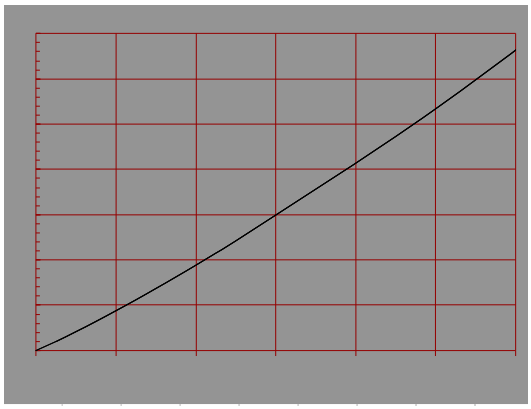


FIG.2: RMS on-state current versus case temperature

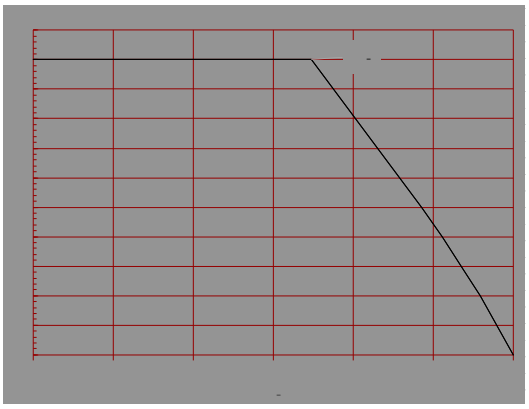


FIG.3: Surge peak on-state current versus number of cycles

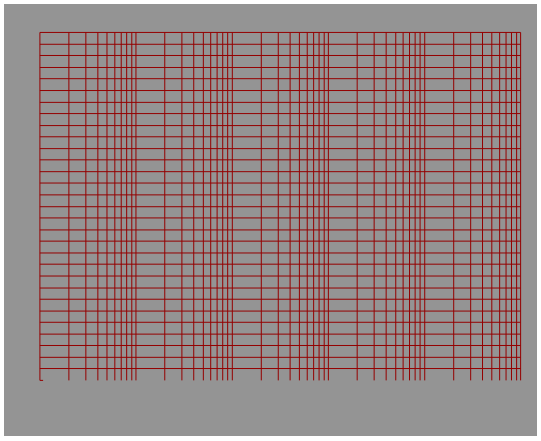
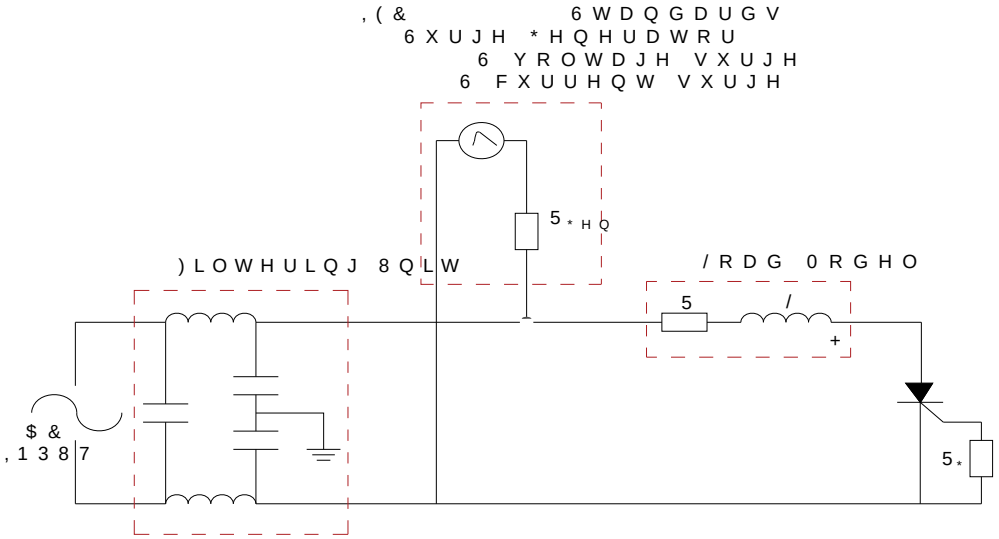


FIG.4: On-state characteristics

FIG. 7 Ö 7HVW FLUFXLW IRU UHVLVWLYH ORDG WR ,(&



h w5 9 wLbD LbC h wa ! ¢ L h b

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT820FH	800	15	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	C h anges
Jun.15, 2023	A.1.0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

t ! /Y ! D 9 a 9 /I ! bL/ ! [5 ! ¢ !

